

**Amendment**

**Clean Claims**

11. (Twice Amended) A high holding voltage LVTSCR-like structure, comprising  
an emitter,  
a drain contact region, and  
a floating drain, wherein the emitter is located so that at least part  
of the drain contact region is located between a gate and the emitter.
12. (Twice Amended) A structure of claim 11, wherein the drain contact region is split into  
at least one first drain portion located near the gate, and at least one second drain portion.
16. (Twice Amended) A structure of claim 12, wherein the floating drain and drain contact  
region are separated by a shallow trench isolation region.